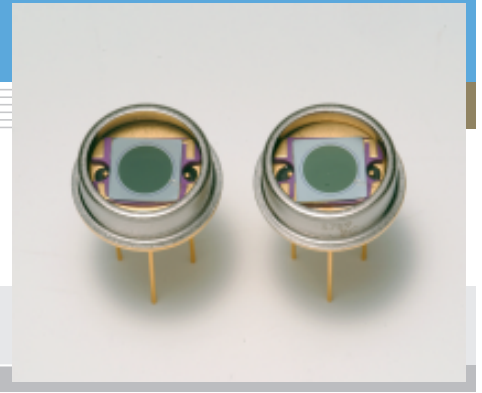


Si PIN photodiode

S3759



Si PIN photodiode for visible to infrared photometry

S3759 is a Si PIN photodiode developed to detect and measure infrared energy emitted from YAG lasers (1.06 μm). Compared to standard Si photodiodes, S3759 delivers exceptionally high sensitivity of 0.38 A/W at 1.06 μm . The PIN structure allows high-speed response and low capacitance. The active area is as large as $\phi 5\text{ mm}$, making optical axis alignment easier.

Features

- High sensitivity in infrared region: 0.38 A/W ($\lambda=1.06\ \mu\text{m}$)
- High-speed response: $t_r=12.5\ \text{ns}$ ($V_R=100\ \text{V}$)
- Low capacitance: $C_t=10\ \text{pF}$ ($V_R=100\ \text{V}$)
- Large active area: $\phi 5\ \text{mm}$
- High reliability: TO-8 metal package

Applications

- YAG laser detection
- Analytical equipment, etc

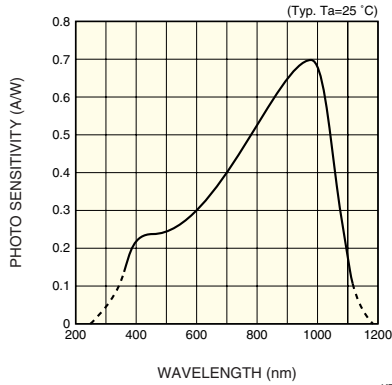
■ Absolute maximum ratings

Parameter	Symbol	Value	Unit
Maximum reverse voltage	$V_R\ \text{Max.}$	150	V
Operating temperature	T_{opr}	-40 to +100	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^{\circ}\text{C}$

■ Electrical and optical characteristics ($T_a=25\ ^{\circ}\text{C}$)

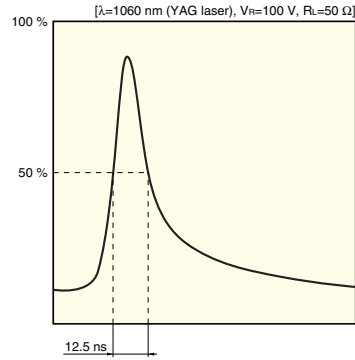
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Spectral response range	λ		-	360 to 1120	-	nm
Peak sensitivity wavelength	λ_p		-	980	-	nm
Photo sensitivity	S	$\lambda=1060\ \text{nm}$	0.3	0.38	-	A/W
Short circuit current	I_{sc}	2856 K, 1000 lx	14	19	-	μA
Dark current	I_D	$V_R=100\ \text{V}$	-	1	10	nA
Rise time	t_r	$\lambda=1060\ \text{nm}$, $V_R=100\ \text{V}$, $R_L=50\ \Omega$	-	12.5	-	ns
Terminal capacitance	C_t	$V_R=100\ \text{V}$, $f=1\ \text{MHz}$	-	10	-	pF

■ Spectral response



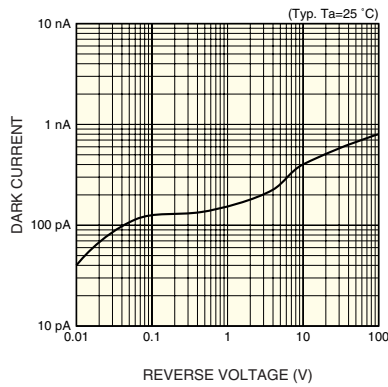
KPINB0279EA

■ Response waveform



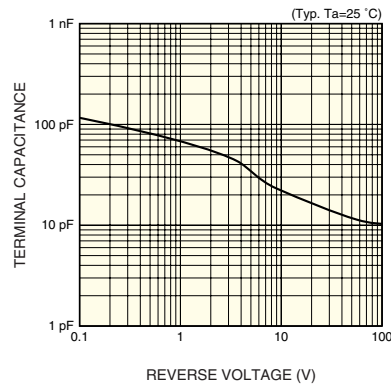
KPINB0280EA

■ Dark current vs. reverse voltage



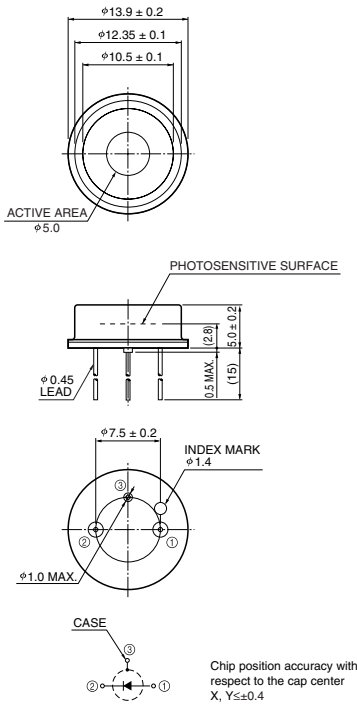
KPINB0281EA

■ Terminal capacitance vs. reverse voltage



KPINB0282EA

■ Dimensional outline (unit: mm)



KPINA0092EA

HAMAMATSU

Information furnished by HAMAMATSU is believed to be reliable. However, no responsibility is assumed for possible inaccuracies or omissions. Specifications are subject to change without notice. No patent rights are granted to any of the circuits described herein. ©2002 Hamamatsu Photonics K.K.

HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Hamamatsu City, 435-8558 Japan, Telephone: (81) 053-434-3311, Fax: (81) 053-434-5184, <http://www.hamamatsu.com>

U.S.A.: Hamamatsu Corporation, 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 08152-3750, Fax: (49) 08152-2658

France: Hamamatsu Photonics France S.A.R.L.: 8, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1/E, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741